

## Silicon Epitaxial Planar Zener Diodes

## BZM55BXXX



LS31(Micro MELF)

LS-31(Micro MELF)  
Glass case MicroMELF  
RoHS compliant

### FEATURE:

1. Fits onto SC-76 / TO-236 footprints
2. MicroMELF package
3. This product is available in AEC-Q101 Compliant and PPAP Capable also.

**Note:** For AEC-Q101 compliant products, please use suffix -AQ in the part number while ordering.

### ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation	$P_{tot}$	500	mW
Junction Temperature	$T_j$	175	°C
Storage Temperature Range	$T_{STG}$	-55to +175	°C

### Thermal Resistance

Thermal Resistance Junction to Ambient	$R_{\theta JA}$	300	°C/W
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### Note:

1. Valid provided that electrodes are kept at ambient temperature.

### ELECTRICAL CHARACTERISTICS at (Ta = 25 °C Unless otherwise specified)

Type	Zener Voltage <sup>1</sup>			Dynamic Resistance			Reverse Leakage Current			Temp coefficient of Zener Voltage TKvz (%/K)
	$V_{Znom}$	$V_{ZT}$	at $I_{ZT}$	$Z_{ZT}$	$Z_{ZK}$	at $I_{ZK}$	$T_a=25^{\circ}C$	$T_a = 125^{\circ}C$	at $V_R$	
	(V)	(V)	(mA)	Max.(Ω)	Max.(Ω)	(mA)	Max.(μA)	Max. (μA)	(V)	
BZM55B1B <sup>2)</sup>	0.75	0.73...0.77	5	8	50	1	-	-	1	-0.26...-0.23
BZM55B2B0	2	1.96...2.04	5	85	600	1	100	200	1	-0.09...-0.06
BZM55B2B2	2.2	2.15...2.25	5	85	600	1	75	160	1	-0.09...-0.06
BZM55B2B4	2.4	2.35...2.45	5	85	600	1	50	100	1	-0.09...-0.06
BZM55B2B7	2.7	2.64...2.76	5	85	600	1	10	50	1	-0.09...-0.06
BZM55B3B0	3	2.94...3.06	5	85	600	1	4	40	1	-0.08...-0.05
BZM55B3B3	3.3	3.23...3.37	5	85	600	1	2	40	1	-0.08...-0.05



Continental Device India Pvt. Limited

An IATF 16949, ISO9001 and ISO 14001 Certified Company



**ELECTRICAL CHARACTERISTICS at** (Ta = 25 °C Unless otherwise specified)

Type	Zener Voltage <sup>1</sup>			Dynamic Resistance			Reverse Leakage Current			Temp coefficient of Zener Voltage
	V <sub>Znom</sub>	V <sub>ZT</sub>	at I <sub>ZT</sub>	Z <sub>ZT</sub>	Z <sub>ZK</sub>	at I <sub>ZK</sub>	T <sub>a</sub> =25°C	T <sub>a</sub> = 125°C	at V <sub>R</sub>	
	(V)	(V)	(mA)	Max.(Ω)	Max.(Ω)	(mA)	Max.(μA)	Max. (μA)	(V)	
BZM55B3B6	3.6	3.52...3.68	5	85	600	1	2	40	1	-0.08...-0.05
BZM55B3B9	3.9	3.82...3.98	5	85	600	1	2	40	1	-0.08...-0.05
BZM55B4B3	4.3	4.21...4.39	5	75	600	1	1	20	1	-0.06...-0.03
BZM55B4B7	4.7	4.6...4.8	5	60	600	1	0.5	10	1	-0.05...+0.02
BZM55B5B1	5.1	4.99...5.21	5	35	550	1	0.1	2	1	-0.02...+0.02
BZM55B5B6	5.6	5.48...5.72	5	25	450	1	0.1	2	1	-0.05...+0.05
BZM55B6B2	6.2	6.07...6.33	5	10	200	1	0.1	2	2	0.03...0.06
BZM55B6B8	6.8	6.66...6.94	5	8	150	1	0.1	2	3	0.03...0.07
BZM55B7B5	7.5	7.35...7.65	5	7	50	1	0.1	2	5	0.03...0.07
BZM55B8B2	8.2	8.03...8.37	5	7	50	1	0.1	2	6.2	0.03...0.08
BZM55B9B1	9.1	8.91...9.29	5	10	50	1	0.1	2	6.8	0.03...0.09
BZM55B10B	10	9.8...10.2	5	15	70	1	0.1	2	7.5	0.03...0.1
BZM55B11B	11	10.78...11.22	5	20	70	1	0.1	2	8.2	0.03...0.11
BZM55B12B	12	11.76...12.24	5	20	90	1	0.1	2	9.1	0.03...0.11
BZM55B13B	13	12.74...13.26	5	26	110	1	0.1	2	10	0.03...0.11
BZM55B15B	15	14.7...15.3	5	30	110	1	0.1	2	11	0.03...0.11
BZM55B16B	16	15.68...16.32	5	40	170	1	0.1	2	12	0.03...0.11
BZM55B18B	18	17.64...18.36	5	50	170	1	0.1	2	13	0.03...0.11
BZM55B20B	20	19.6...20.4	5	55	220	1	0.1	2	15	0.03...0.11
BZM55B22B	22	21.56...22.44	5	55	220	1	0.1	2	16	0.04...0.12
BZM55B24B	24	23.52...24.48	5	80	220	1	0.1	2	18	0.04...0.12
BZM55B27B	27	26.46...27.54	5	80	220	1	0.1	2	20	0.04...0.12
BZM55B30B	30	29.4...30.6	5	80	220	1	0.1	2	22	0.04...0.12
BZM55B33B	33	32.34...33.66	5	80	220	1	0.1	2	24	0.04...0.12
BZM55B36B	36	35.28...36.72	5	80	220	1	0.1	2	27	0.04...0.12
BZM55B39B	39	38.22...39.78	2.5	90	500	0.5	0.1	5	30	0.04...0.12
BZM55B43B	43	42.14...43.86	2.5	90	500	0.5	0.1	5	33	0.04...0.12
BZM55B47B	47	46.06...47.94	2.5	110	600	0.5	0.1	5	36	0.04...0.12
BZM55B51B	51	49.98...52.02	2.5	125	700	0.5	0.1	10	39	0.04...0.12
BZM55B56B	56	54.88...57.12	2.5	135	700	0.5	0.1	10	43	0.04...0.12
BZM55B62B	62	60.76...63.24	2.5	150	1000	0.5	0.1	10	47	0.04...0.12
BZM55B68B	68	66.64...69.36	2.5	200	1000	0.5	0.1	10	51	0.04...0.12
BZM55B75B	75	73.5...76.5	2.5	250	1000	0.5	0.1	10	56	0.04...0.12

1. Tested with pulse t<sub>p</sub> = 20 ms.

BZM55BXXX  
Rev0 27072022EGL

### Recommended Reflow Solder Profiles

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.

Figure 1

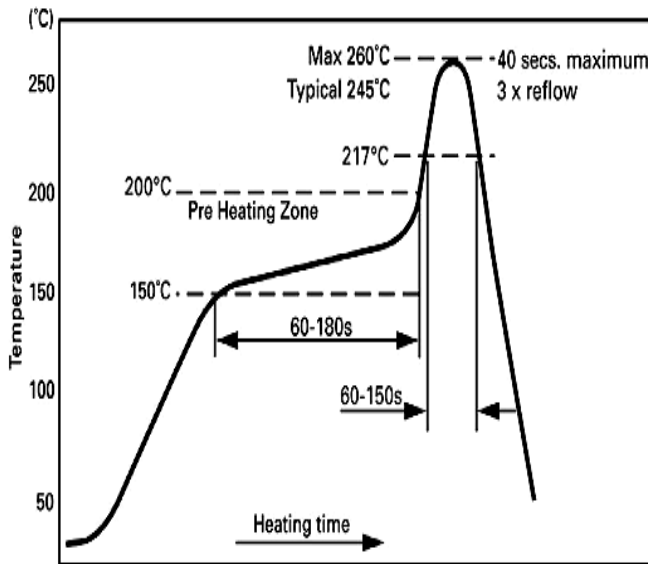
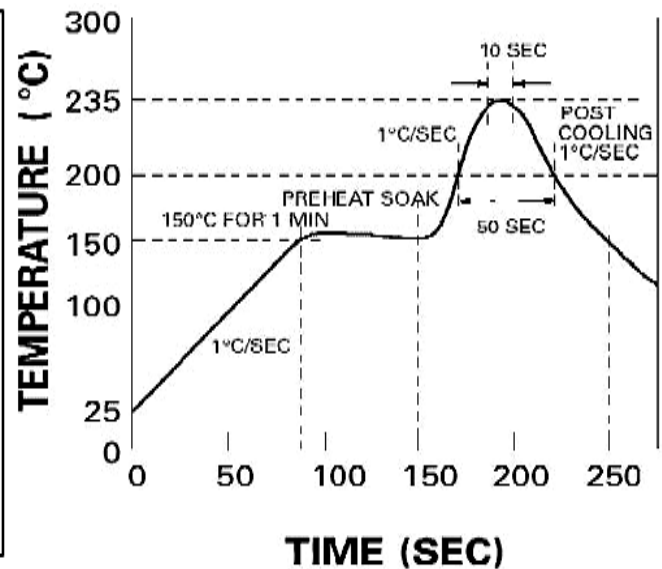


Figure 2



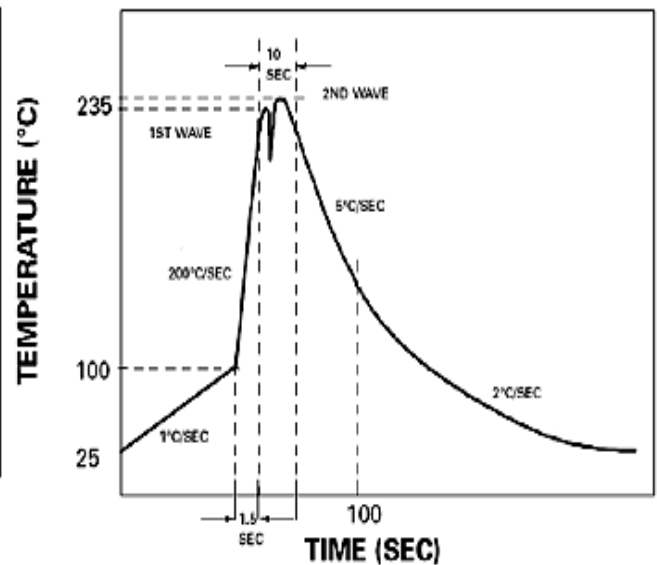
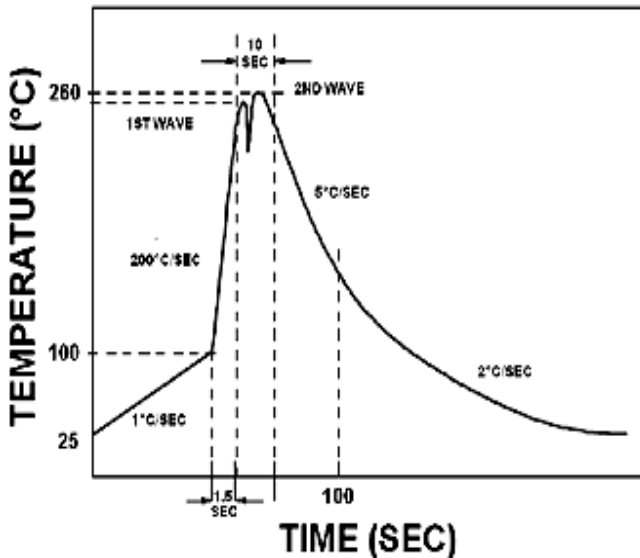
### Reflow profiles in tabular form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
<b>Preheat</b>		
– Temperature Range	150-170°C	150-200°C
– Time	60-180 seconds	60-180 seconds
Time maintained above:		
– Temperature	200°C	217°C
– Tim	30-50 seconds	60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max

### Recommended Wave Solder Profiles

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used

The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder



### Wave Profiles in Tabular Form

Profile Feature	Sn-Pb System	Pb-free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max.

## TYPICAL CHARACTERISTIC CURVES

Fig 1: Zener Characteristics Curve

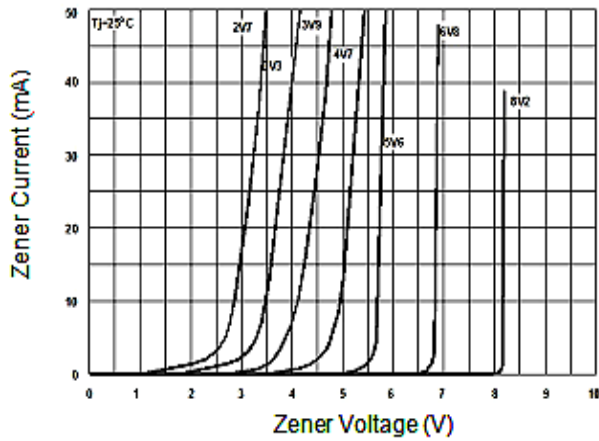


Fig 3: Zener Characteristics Curve

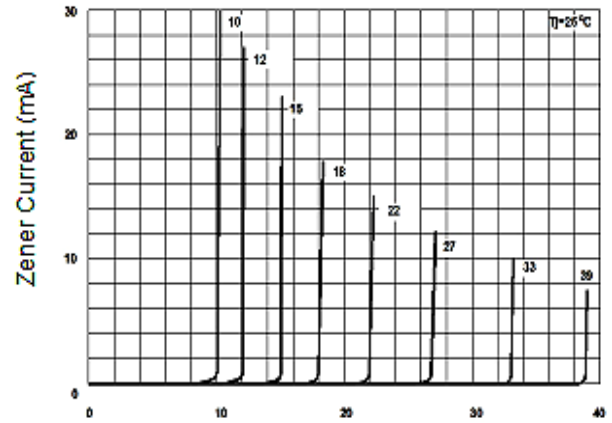
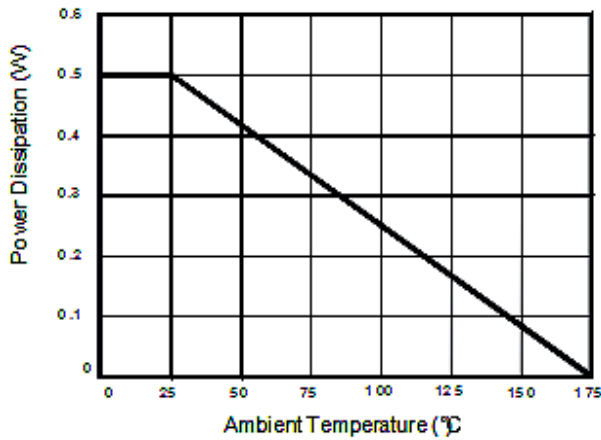
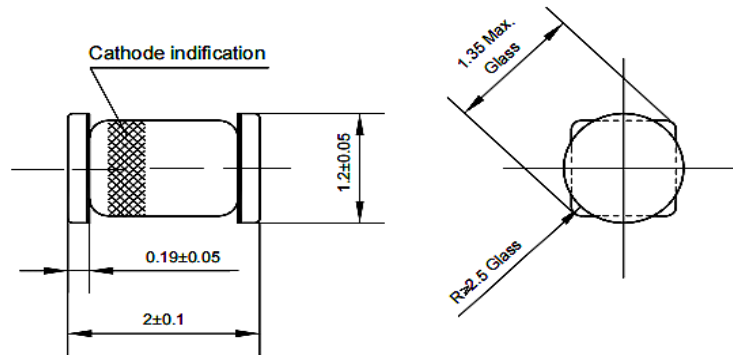


Fig 2: Power Derating Curve



## Package Details

LS-31 (Micro MELF) Glass case MicroMELF



All Dimensions are in mm



### Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- Temperature 5 °C to 30 °C
- Humidity between 40 to 70 %RH
- Air should be clean.
- Avoid harmful gas or dust.
- Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- Avoid rapid change of temperature.
- Avoid condensation.
- Mechanical stress such as vibration and impact shall be avoided.
- The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

#### **Shelf Life of CDIL Products**

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

#### **Floor Life of CDIL Products and MSL Level**

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

JEDEC MSL Level		
Level	Time	Condition
1	Unlimited	≤30 °C / 85% RH
2	1 Year	≤30 °C / 60% RH
2a	4 Weeks	≤30 °C / 60% RH
3	168 Hours	≤30 °C / 60% RH
4	72 Hours	≤30 °C / 60% RH
5	48 Hours	≤30 °C / 60% RH
5a	24 Hours	≤30 °C / 60% RH
6	Time on Label(TOL)	≤30 °C / 60% RH



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## Customer Notes

### Component Disposal Instructions

1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

### Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



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